

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (currently amended) A lateral double-diffused metal oxide semiconductor (LDMOS) device comprising:
  - a gate region;
  - a body region under the gate region; and
  - an enhanced drift region under the gate region, whereby the enhanced drift region purposely overlaps the body region;
    - a drain region within the enhanced drift region such that the enhanced drift region is under the entire drain region; and
      - a layer, well, or substrate under the enhanced drift region and the body region, wherein the layer, well, or substrate has the same conductivity type as the enhanced drift region.
2. (cancelled)
3. (cancelled)
4. (cancelled)
5. (currently amended) A lateral double-diffused metal oxide semiconductor (LDMOS)

device comprising:

a gate region, the gate region including a gate and gate oxide;

a body region under the gate region;

an enhanced drift region under the gate region whereby the enhanced drift region purposely overlaps the body region; and

a drain region within the enhanced drift region such that the enhanced drift region is under the entire drain region; and

a layer, well or substrate under the enhanced drift region and the body region,  
wherein the layer, well or substrate has the same conductivity type as the enhanced drift region.

6. (cancelled)

7. (original) The LDMOS device of claim 5 wherein the enhanced drift region purposely overlaps the lateral tail of the body region.

8. (withdrawn)

9. (withdrawn)

10. (withdrawn)

11. (withdrawn)

12. (withdrawn)

13. (withdrawn)

14. (withdrawn)

15. (new) The LDMOS device of claim 1 wherein the enhanced drift region purposely overlaps the lateral tail of the body region.

16. (new). The LDMOS device of claim 1 wherein the conductivity type of the enhanced drift region and the layer, well, or substrate is N-type.

17. (new). The LDMOS device of claim 1 wherein the conductivity type of the enhanced drift region and the layer, well, or substrate is P-type.

18. (new). The LDMOS device of claim 1 wherein the layer, well, or substrate is an epitaxial layer, and further comprising a buried layer provided under the epitaxial layer and above a substrate, the buried layer having the conductivity type of the epitaxial layer and a different conductivity type than the substrate.

19. (new). The LDMOS device of claim 5 wherein the conductivity type of the enhanced drift region and the layer, well, or substrate is N-type.

20. (new). The LDMOS device of claim 5 wherein the conductivity type of the enhanced drift region and the layer, well, or substrate is P-type.

21. (new). The LDMOS device of claim 5 wherein the layer, well, or substrate is an epitaxial layer, and further comprising a buried layer provided under the epitaxial layer and above a substrate, the buried layer having the conductivity type of the epitaxial layer and a different conductivity type than the substrate.